







LM6171

SNOS745D - MAY 1998 - REVISED NOVEMBER 2023

LM6171 High-Speed, Low-Power, Low-Distortion Voltage Feedback Amplifier

1 Features

Typical unless otherwise noted

Easy-to-use voltage feedback topology

Very high slew rate: 3600 V/µs

Wide unity-gain-bandwidth product: 76 MHz

-3-dB frequency at A_V = +2: 75 MHz

Low supply current: 2.5 mA

High CMRR: 110 dB

High open-loop gain: 90 dB

Specified for ±15-V and ±5-V operation

2 Applications

Multimedia broadcast systems

Line driver, switch

Video amplifier

NTSC, PAL® and SECAM systems

ADC/DAC buffer

HDTV amplifier

Pulse amplifier and peak detector

Instrumentation amplifier

Active filter

3 Description

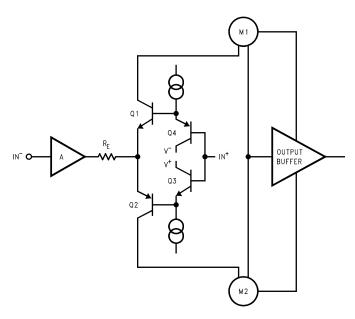
The LM6171 is a high-speed, unity-gain-stable voltage-feedback amplifier. The LM6171 offers a high slew rate of 3600 V/µs and a unity-gain bandwidth of 100 MHz while consuming only 2.5 mA of supply current. The LM6171 has very impressive ac and dc performance that is a great benefit for high-speed signal processing and video applications.

The ±15-V power supplies allow for large signal swings and give greater dynamic range and signalto-noise ratio (SNR). The LM6171 has a high output current drive, low spurious-free dynamic range (SFDR) and total harmonic distortion (THD), and is an excellent choice for analog-to-digital converter (ADC) and digital-to-analog converter (DAC) systems. The LM6171 is specified for ±5-V operation for portable applications.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾
I M6171	D (SOIC, 8)	4.9 mm × 6 mm
LIVIOT7T	P (PDIP, 8)	9.81 mm × 9.43 mm

- For more information, see Section 10.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Simplified Schematic



Table of Contents

1 Features1	6.3 Feature Description	26
2 Applications1	6.4 Device Functional Modes	
3 Description1	7 Application and Implementation	27
4 Pin Configuration and Functions2	7.1 Application Information	27
5 Specifications3	7.2 Typical Applications	30
5.1 Absolute Maximum Ratings3	7.3 Power Supply Recommendations	
5.2 ESD Ratings	7.4 Layout	31
5.3 Recommended Operating Conditions3	8 Device and Documentation Support	
5.4 Thermal Information3	8.1 Receiving Notification of Documentation Updates.	32
5.5 Electrical Characteristics: ±15 V4	8.2 Support Resources	32
5.6 Electrical Characteristics: ±5 V6	8.3 Trademarks	
5.7 Typical Characteristics: LM6171A Only8	8.4 Electrostatic Discharge Caution	32
5.8 Typical Characteristics17	8.5 Glossary	
6 Detailed Description26	9 Revision History	
6.1 Overview	10 Mechanical, Packaging, and Orderable	
6.2 Functional Block Diagram26	Information	33

4 Pin Configuration and Functions

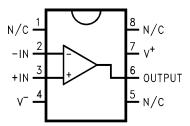


Figure 4-1. D Package, 8-Pin SOIC P Package, 8-Pin PDIP (Top View)

Table 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.	ITPE	DESCRIPTION
-IN	2	ı	Negative input pin
+IN	3	I	Positive input pin
N/C	1, 5, 8	_	This pin is not internally connected; leave floating or connect to any other pin on the device.
OUTPUT	6	0	Output pin.
V-	4	I/O	Negative supply voltage pin.
V ⁺	7	I/O	Positive supply voltage pin.

(1) Signal types: I = input, O = output, I/O = input or output.



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

		MIN	MAX	UNIT
Vs	Supply voltage (V ⁺ – V ⁻)		36	V
V _I	Differential input voltage		±10	V
V _{CM}	Common-mode voltage	(V ⁻) - 0.3	(V ⁺) + 0.3	V
I _{IN}	Input current		±10	mA
I _{SC}	Output current short to ground ⁽³⁾		Continuous	А
T _{stg}	Storage temperature	-65	150	°C
TJ	Junction temperature ⁽⁴⁾		150	°C
т	Infrared or convection reflow (20 seconds)		235	°C
T _{SOLDER}	Wave soldering lead temp (10 seconds)		260	C

- (1) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/Distributors for availability and specifications.
- (2) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (3) Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C.
- (4) The maximum power dissipation is a function of T_{J(MAX)}, R_{θ,JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)}-T_A)/R_{θ,JA}. All numbers apply for packages soldered directly into a PC board.

5.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
	discharge	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP155 states that 2500-V HBM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	TYP MAX	UNIT
V _S	Supply voltage	5.5	34	V
T _A	Ambient temperature	-40	85	°C

5.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	D (SOIC) A Version	D (SOIC) B Version	P (PDIP)	UNIT
		8 PINS	8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	122.5	172	108	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	64.7	62.4	52.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	65.9	55.7	51.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	17.6	16.5	6.8	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	65.1	55.1	51.1	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



5.5 Electrical Characteristics: ±15 V

at $T_J = 25^{\circ}$ C, $V^+ = 15$ V, $V^- = -15$ V, $V_{CM} = 0$ V, and $R_L = 1$ k Ω (unless otherwise noted)

	PARAMETER	TEST CON	IDITIONS	MIN ⁽²⁾	TYP ⁽¹⁾	MAX ⁽²⁾	UNIT
		18404748			1.5	3	
	Input offset voltage	LM6171A	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		-	5	.,
Vos					1.5	6	mV
		LM6171B	T _A = -40°C to +85°C			8	
TCV _{OS}	Input offset voltage average drift				6		μV/°C
					1	3	-
I _B	Input bias current	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			-	4	
					0.03	2	μΑ
los	Input offset current	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$				3	
		Common-mode			40		
R _{IN}	Input resistance	Differential-mode			4.9		ΜΩ
R _O	Open-loop output resistance				14		Ω
		LM6171A,		80	110		
		$V_{CM} = \pm 10 \text{ V}$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	75			
CMRR	Common-mode rejection ratio	LM6171B,		75	110		dB
		V _{CM} = ±10 V	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			
		LM6171A,		85	95		dB
		$V_S = \pm 5 \text{ V to } \pm 15 \text{ V}$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	80			
PSRR	Power supply rejection ratio	LM6171B,		80	95		
		$V_S = \pm 5 \text{ V to } \pm 15 \text{ V}$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	75			
V _{CM}	Input common-mode voltage	CMRR > 60 dB			±13.5		V
		$R_L = 1 \text{ k}\Omega, V_{OUT} = \pm 5 \text{ V}$		80	90		
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	70			٦D
A_V	Large signal voltage gain ⁽³⁾	R _L = 100 Ω, V _{OUT} = ±5 V		70	83		dB
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	60			
		$R_L = 1 \text{ k}\Omega$, sourcing		12.5	13.3		
			$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	12			
		D. Alico stations		-12.5	-13.3		ļ
.,	Output owing	$R_L = 1 \text{ k}\Omega$, sinking	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	-12			17
Vo	Output swing	D = 100 O sourcing		9	11.6		V
		$R_L = 100 \Omega$, sourcing	T _A = -40°C to +85°C	8.5			
		$R_L = 100 \Omega$, sinking		-9	-10.5		
		TL - 100 12, SINKING	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	-8.5			
		Sourcing B = 100 C		90	116		
	Continuous output current (open	Sourcing, $R_L = 100 \Omega$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	85			m ^
	loop) ⁽⁴⁾	Sinking P = 100 0		90	105		mA
		Sinking, $R_L = 100 \Omega$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	85			
	Continuous output current (in linear	Sourcing, $R_L = 100 \Omega$			100		mΛ
	region)	Sinking, $R_L = 100 \Omega$			80		- mA
	Output short circuit current	Sourcing			135		mA
I _{SC}	Output short circuit current	Sinking			135		
	Supply current				2.5	mΔ	
l _S	Supply current	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$			-	4.5	шА

5.5 Electrical Characteristics: ±15 V (continued)

at $T_{J} = 25^{\circ}$ C, $V^{+} = 15$ V, $V^{-} = -15$ V, $V_{CM} = 0$ V, and $R_{J} = 1$ k Ω (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	MIN ⁽²⁾	TYP ⁽¹⁾	MAX ⁽²⁾	UNIT
CD	Slew rate ⁽⁵⁾	A _V = +2, V _{IN} = 13 V _{PP}			3600		\//
SR	Siew rate(4)	$A_V = +2, V_{IN} = 10 V_{PP}$			3000		V/µs
	Limites are in the productional by	LM6171A			76		MHz
	Unity-gain bandwidth	LM6171B			100		MHz
		L MG 171 A	A _V = +1		200		
	2 dD fra muser au	LM6171A	A _V = +2		75		NAL 1-
	−3-dB frequency	LMC474D	A _V = +1		160		MHz
		LM6171B	A _V = +2		62		
	Dhoos morain	LM6171A		58			D
Ψm	Phase margin	LM6171B			40		Deg
	Cattling time = (0.40/)	$A_V = -1$, $V_{OUT} = \pm 5$ V,	LM6171A		21		
t _s	Settling time (0.1%)	R _L = 500 Ω	LM6171B		48		ns
	Decreasion delect	$A_V = -2$, $V_{IN} = \pm 5$ V,	LM6171A		4.1		
t _p	Propagation delay	R _L = 500 Ω	LM6171B		6		ns
A _D	Differential gain ⁽⁶⁾				0.03		%
ΦD	Differential phase ⁽⁶⁾				0.5		0
e _n	Input-referred voltage noise	f = 10 kHz			12		nV/√Hz
i _n	Input-referred current noise	f = 10 kHz			1		pA/√Hz

⁽¹⁾ Typical values represent the most likely parametric norm

⁽²⁾ All limits are specified by testing or statistical analysis.

⁽³⁾ Large-signal voltage gain is the total output swing divided by the input signal required to produce that swing. For V_S = ±15 V, V_{OUT} = ±5 V. For V_S = +5 V, V_{OUT} = ±1 V.

⁽⁴⁾ The open-loop output current is the output swing with the $100-\Omega$ load resistor divided by that resistor.

⁽⁵⁾ Slew rate is the average of the rising and falling slew rates.

⁽⁶⁾ Differential gain and phase are measured with $A_V = +2$, $V_{IN} = 1$ V_{PP} at 3.58 MHz and both input and output 75 Ω terminated.



5.6 Electrical Characteristics: ±5 V

at T $_J$ = 25°C, V+ = 5 V, V^- = -5 V, V $_{CM}$ = 0 V, and R $_L$ = 1 k Ω (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN ⁽²⁾	TYP ⁽¹⁾	MAX ⁽²⁾	UNIT
		I M6171 ^			1.2	3	
. ,		LM6171A	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			5	
Vos	Input offset voltage	LM0474B			1.2	6	mV
		LM6171B	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$			8	
TCVos	Input offset voltage average drift				4		μV/°C
					1	2.5	
I _B	Input bias current	T _A = -40°C to +85°C				3.5	
					0.03	1.5	μA
los	Input offset current	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$				2.2	
		Common-mode			40		
R _{IN}	Input resistance	Differential-mode			4.9		ΜΩ
R _O	Open loop output resistance				14		Ω
		LM6171A,		80	105		
		$V_{CM} = \pm 2.5 \text{ V}$	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	75			
CMRR	Common-mode rejection ratio	LM6171B,		75	105		dB
		V _{CM} = ±2.5 V	T _A = -40°C to +85°C	70			
		LM6171A,		85	95		
		$V_S = \pm 5 \text{ V to } \pm 15 \text{ V}$	T _A = -40°C to +85°C	80			dB
PSRR	Power supply rejection ratio	LM6171B, V _S = ±5 V to ±15 V	7	80	95		
			T _A = -40°C to +85°C	75			
			LM6171A		±3.2		
V_{CM}	Input common-mode voltage	CMRR > 60 dB	LM6171B		±3.7		V
		$R_L = 1 k\Omega,$ $V_{OUT} = \pm 1 V$		75	84		
			T _A = -40°C to +85°C	65			-
A_V	Large signal voltage gain ⁽³⁾	R_L = 100 Ω, V_{OUT} = ±1 V R_L = 1 kΩ, sourcing	A 10 0 10 00 0	70	80		dB
			T _A = -40°C to +85°C	60			
			, , , , , , , , , , , , , , , , , , ,	3.2	3.5		
			T _A = -40°C to +85°C	3			
			, , , , , , , , , , , , , , , , , , ,	-3.2	-3.4		
		$R_L = 1 k\Omega$, sinking	T _A = -40°C to +85°C	-3			
V _O	Output swing		1A 10 0 10 100 0	2.8	3.2		V
		R_L = 100 Ω, sourcing	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	2.5			
			1A 10 0 10 100 0	-2.8	-3.0		
		R_L = 100 Ω, sinking	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	-2.5			
			A 15 5 5 5 5	28	32		
	Continuous output ourrent (ones	Sourcing, $R_L = 100 \Omega$	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	25			
	Continuous output current (open loop) ⁽⁴⁾		14 10 0 10 100 0	28	30		
		Sinking, $R_L = 100 \Omega$	$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$	25			
		Sourcing	1.A 10 0 10 100 0	20	130		mA
sc	Output short circuit current	Sinking			100		
					2.3	3	
S	Supply current	T _A = -40°C to +85°C			2.0	3.5	
		$A_V = +2$, $V_{IN} = 3.5 V_{PP}$			750	0.0	
SR	Slew rate ⁽⁵⁾						V/µs
		$A_V = +2, V_{IN} = 2 V_{PP}$			450		

5.6 Electrical Characteristics: ±5 V (continued)

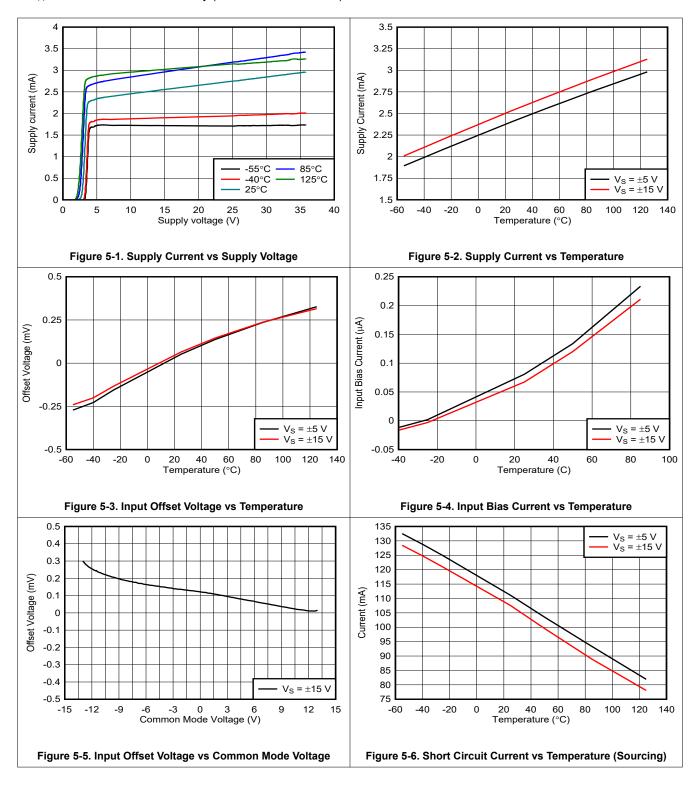
at $T_J = 25^{\circ}$ C, $V^+ = 5$ V, $V^- = -5$ V, $V_{CM} = 0$ V, and $R_L = 1$ k Ω (unless otherwise noted)

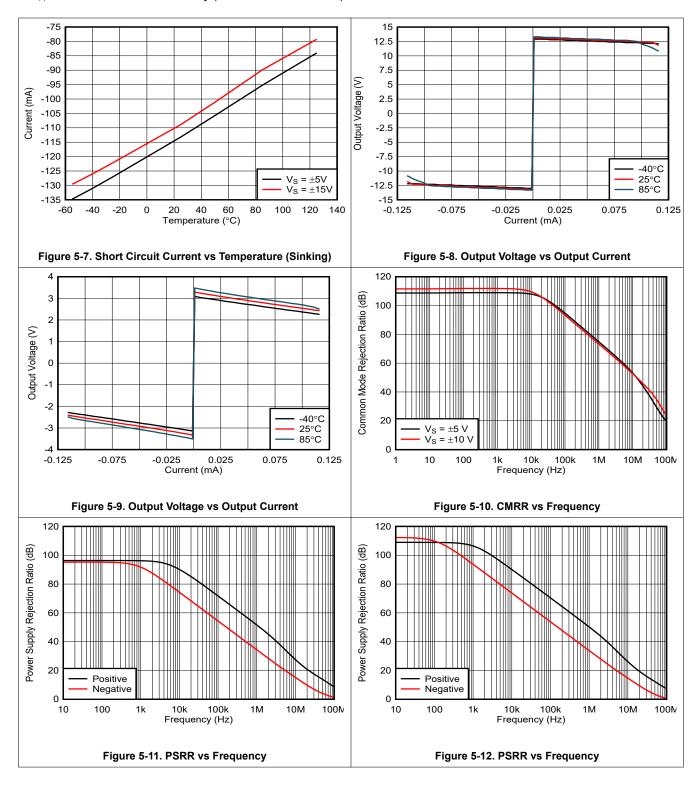
	PARAMETER	TEST CO	NDITIONS	MIN ⁽²⁾	TYP ⁽¹⁾	MAX ⁽²⁾	UNIT
	Unity goin bondwidth	LM6171A	LM6171A		70		MHz
	Unity-gain bandwidth	LM6171B			70		IVI□Z
		∐ M6171Δ	A _V = +1		190		
	2 dD fraguency		A _V = +2		75		MHz
	−3-dB frequency	LM6474D	A _V = +1		130		IVI□Z
		LM6171B	A _V = +2		45		
ϕ_{m}	Phase margin		1		57		Deg
	Cottling time (0.10/)	$A_V = -1$, $V_{OUT} = \pm 1 V$, $R_L = 500 \Omega$	LM6171A		25	200	
t _s	Settling time (0.1%)		LM6171B		60		ns
	Drangation delay	$A_V = -2$, $V_{IN} = \pm 1$ V,	LM6171A		4.5		
t _p	Propagation delay	opagation delay $ \begin{array}{c c} R_{L} = 500 \ \Omega \end{array} $	LM6171B		8		ns
A_D	Differential gain ⁽⁶⁾		1		0.04		%
ϕ_D	Differential phase ⁽⁶⁾				0.7		0
e _n	Input-referred voltage noise	f = 10 kHz			11		nV/√Hz
in	Input-referred current noise	f = 10 kHz			1		pA/√Hz

- (1) Typical values represent the most likely parametric norm
- (2) All limits are specified by testing or statistical analysis.
- (3) Large-signal voltage gain is the total output swing divided by the input signal required to produce that swing. For $V_S = \pm 15 \text{ V}$, $V_{OUT} = \pm 5 \text{ V}$. For $V_S = \pm 5 \text{ V}$, $V_{OUT} = \pm 1 \text{ V}$
- (4) The open-loop output current is the output swing with the $100-\Omega$ load resistor divided by that resistor.
- (5) Slew rate is the average of the rising and falling slew rates.
- (6) Differential gain and phase are measured with $A_V = +2$, $V_{IN} = 1$ V_{PP} at 3.58 MHz and both input and output 75 Ω terminated.

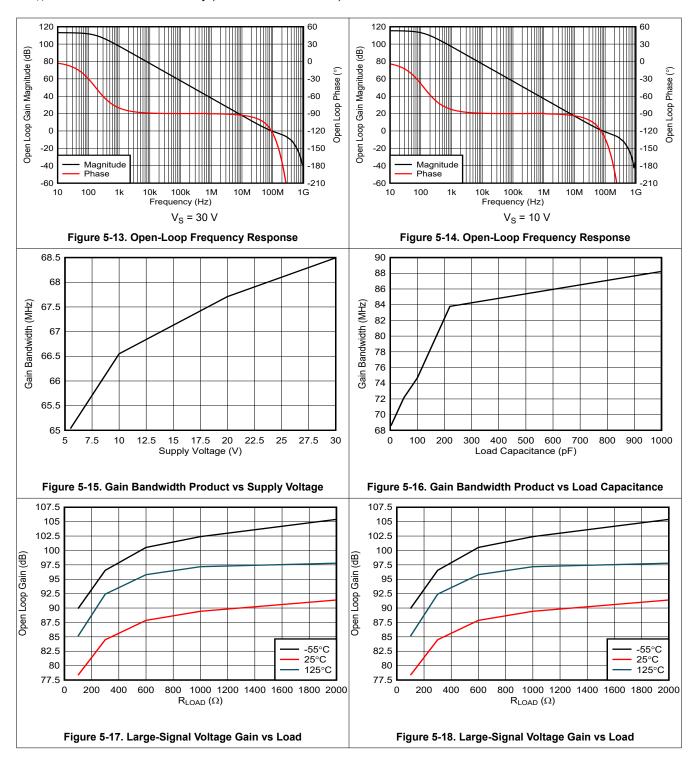


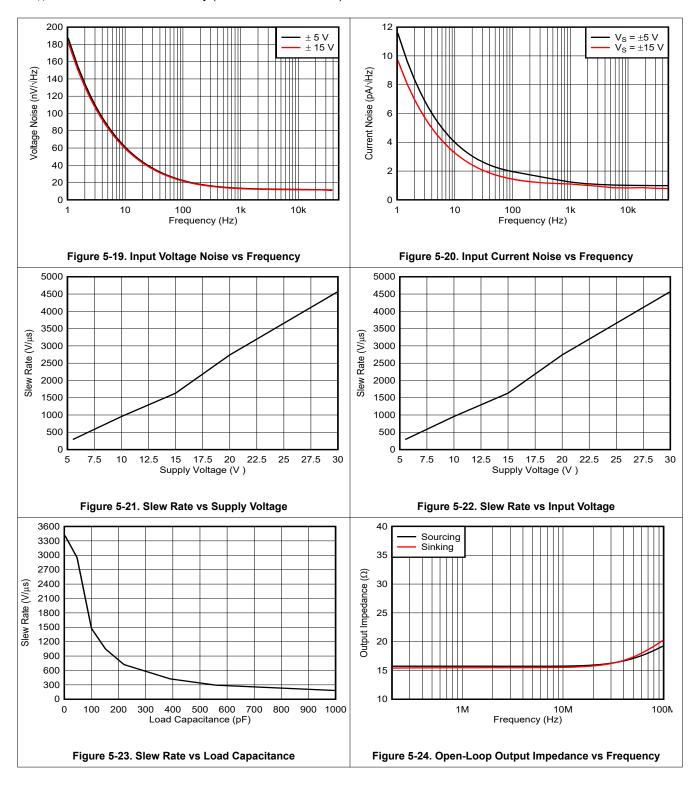
5.7 Typical Characteristics: LM6171A Only



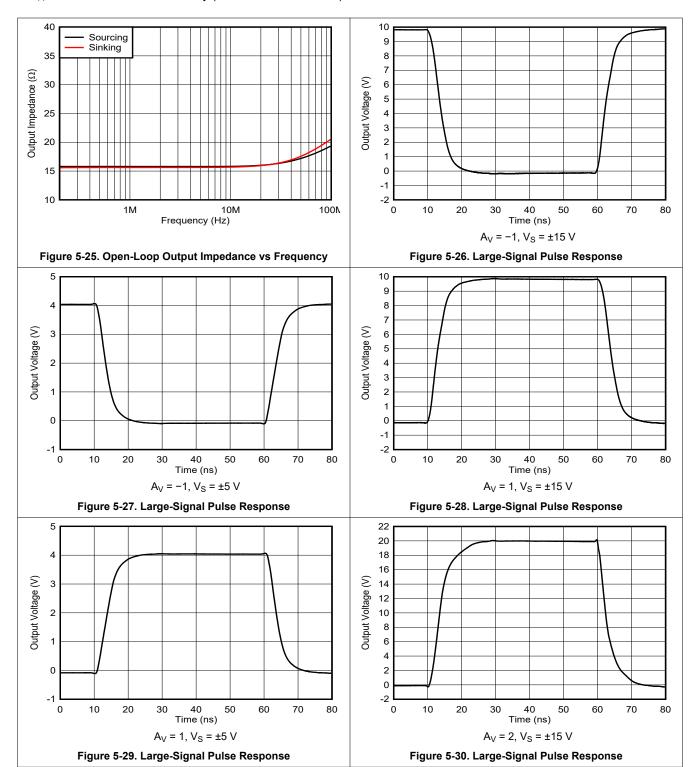


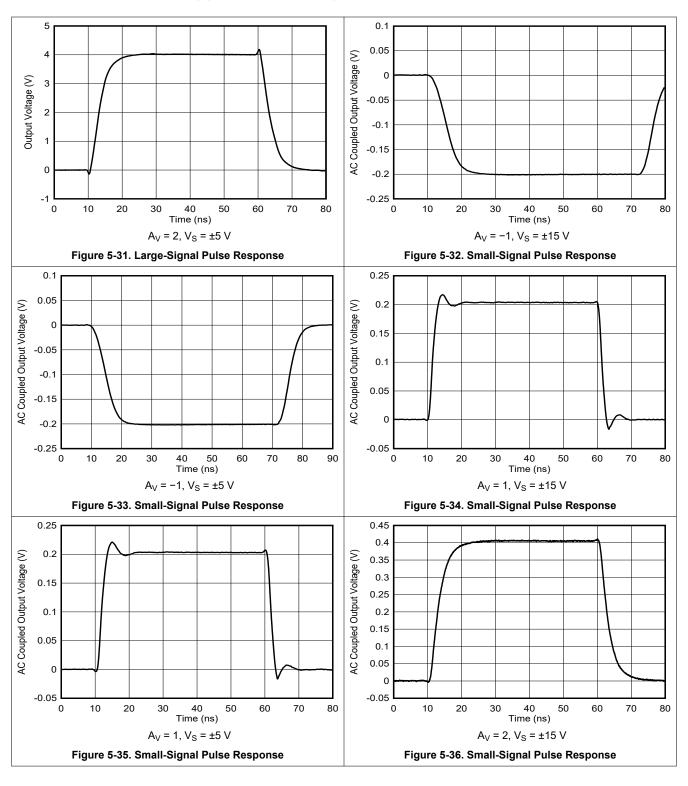




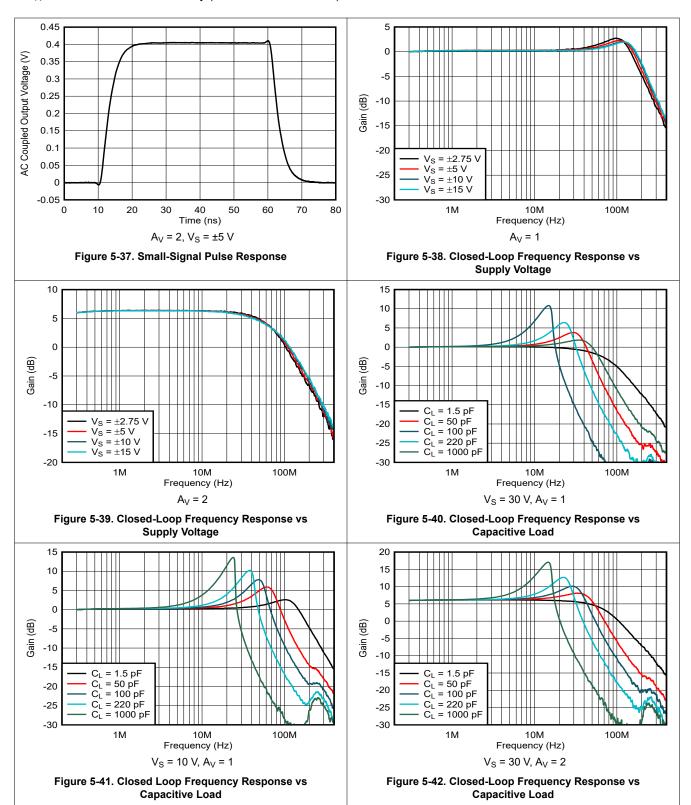


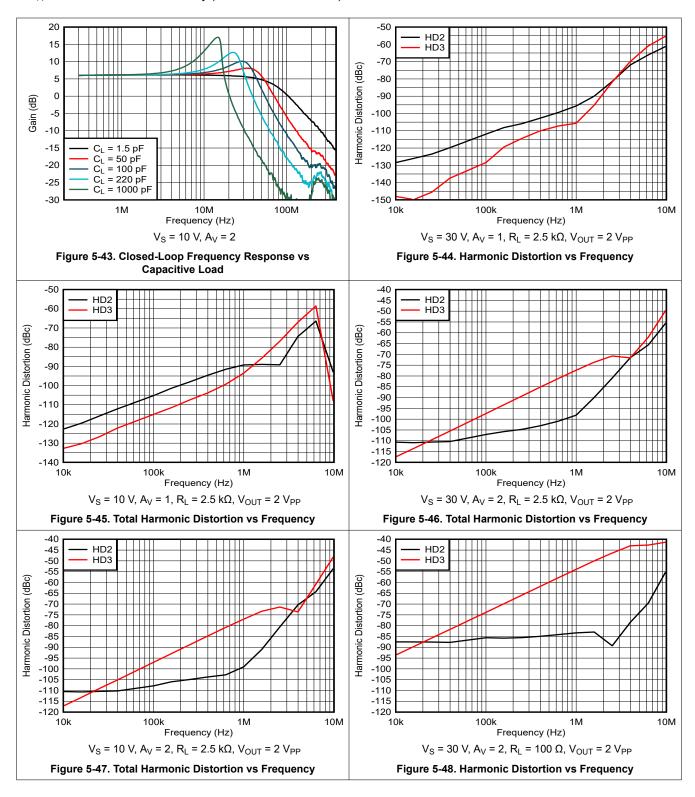






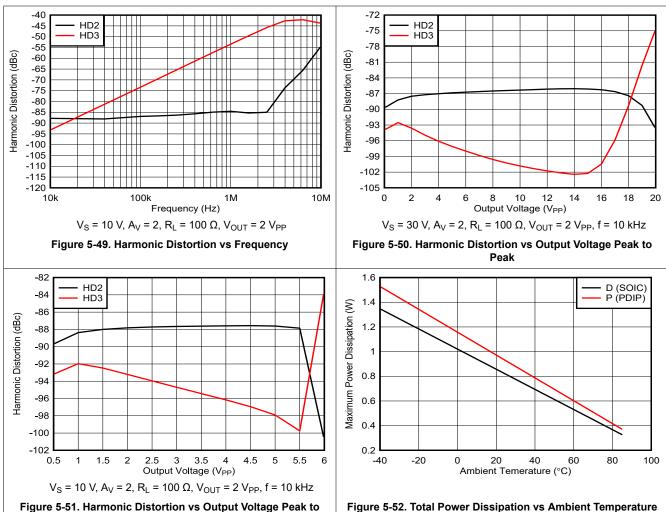






at T_A = 25°C, and for LM6171A only (unless otherwise noted)

Peak



5.8 Typical Characteristics

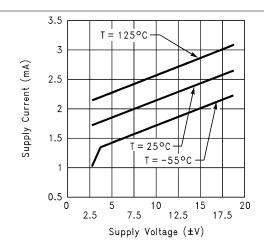


Figure 5-53. Supply Current vs Supply Voltage

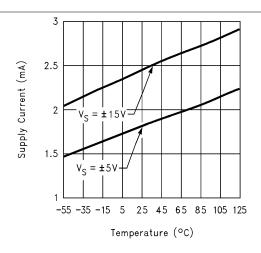


Figure 5-54. Supply Current vs Temperature

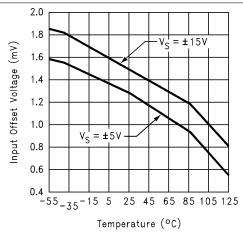


Figure 5-55. Input Offset Voltage vs Temperature

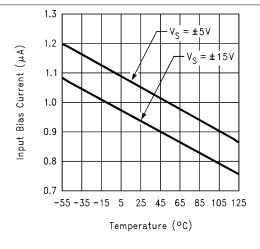


Figure 5-56. Input Bias Current vs Temperature

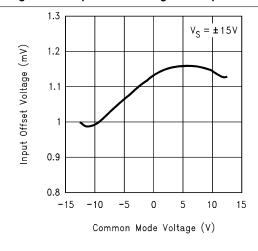


Figure 5-57. Input Offset Voltage vs Common Mode Voltage

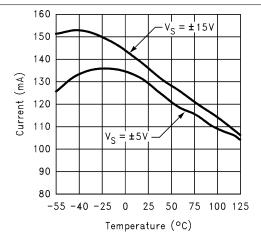


Figure 5-58. Short Circuit Current vs Temperature (Sourcing)



at T_A = 25°C (unless otherwise noted)

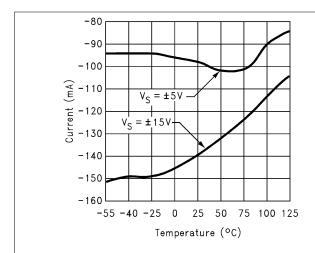


Figure 5-59. Short Circuit Current vs Temperature (Sinking)

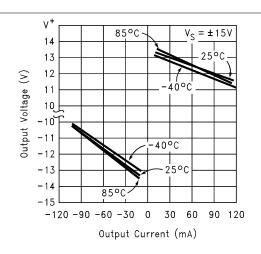


Figure 5-60. Output Voltage vs Output Current

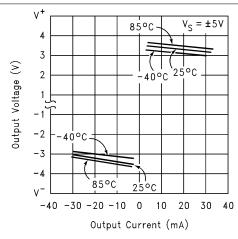


Figure 5-61. Output Voltage vs Output Current

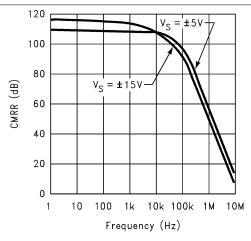
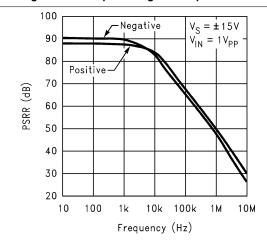


Figure 5-62. CMRR vs Frequency





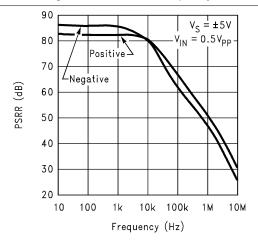


Figure 5-64. PSRR vs Frequency

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated

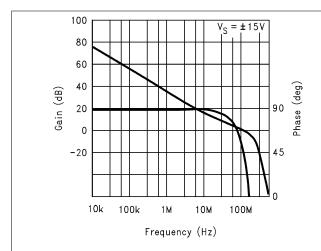


Figure 5-65. Open-Loop Frequency Response

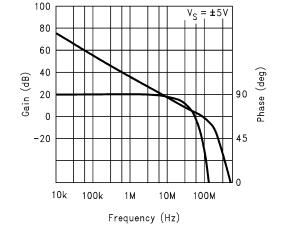


Figure 5-66. Open-Loop Frequency Response

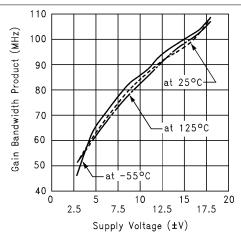


Figure 5-67. Gain Bandwidth Product vs Supply Voltage

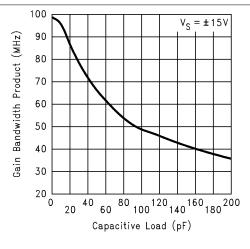


Figure 5-68. Gain Bandwidth Product vs Load Capacitance

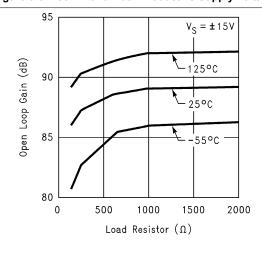


Figure 5-69. Large-Signal Voltage Gain vs Load

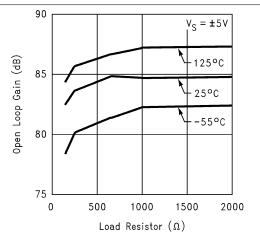


Figure 5-70. Large-Signal Voltage Gain vs Load



at T_A = 25°C (unless otherwise noted)

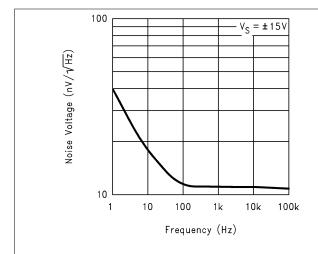


Figure 5-71. Input Voltage Noise vs Frequency

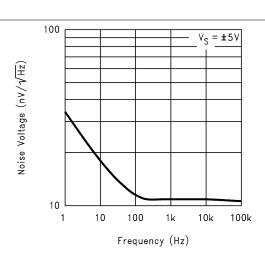


Figure 5-72. Input Voltage Noise vs Frequency

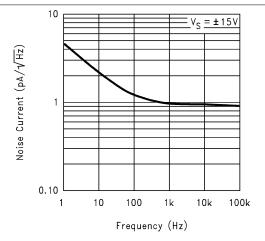


Figure 5-73. Input Current Noise vs Frequency

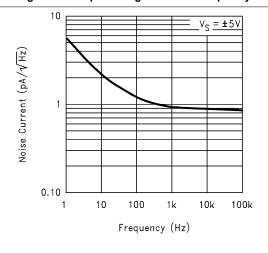


Figure 5-74. Input Current Noise vs Frequency

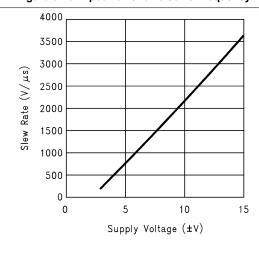


Figure 5-75. Slew Rate vs Supply Voltage

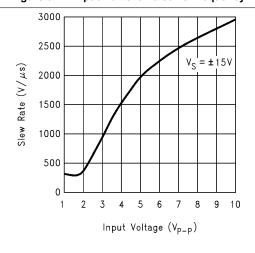


Figure 5-76. Slew Rate vs Input Voltage

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated

at T_A = 25°C (unless otherwise noted)

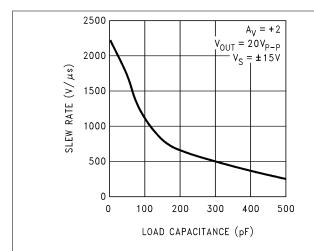


Figure 5-77. Slew Rate vs Load Capacitance

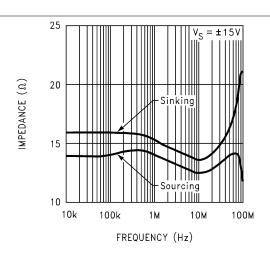


Figure 5-78. Open-Loop Output Impedance vs Frequency

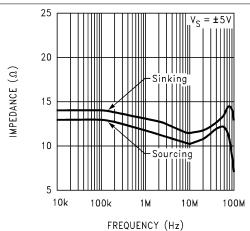


Figure 5-79. Open-Loop Output Impedance vs Frequency

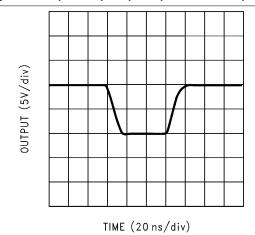


Figure 5-80. Large-Signal Pulse Response

 $A_V = -1$, $V_S = \pm 15 V$

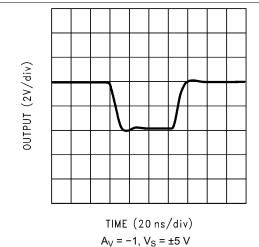


Figure 5-81. Large-Signal Pulse Response

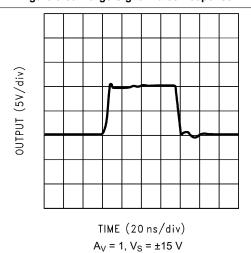
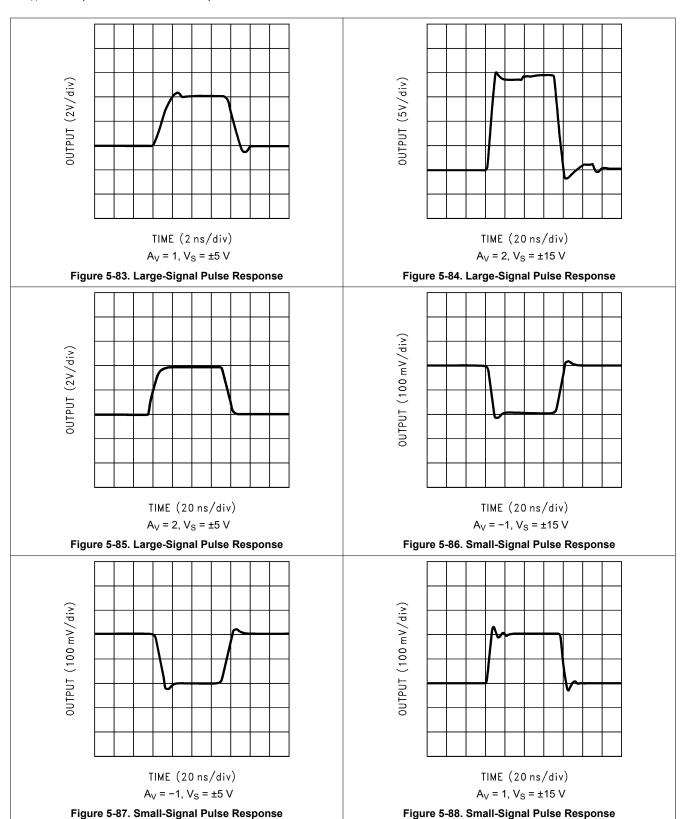
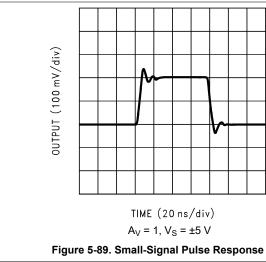
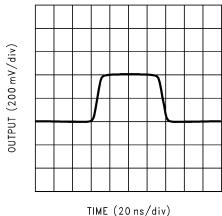


Figure 5-82. Large-Signal Pulse Response









 A_V = 2, V_S = $\pm 5~V$ Figure 5-91. Small-Signal Pulse Response

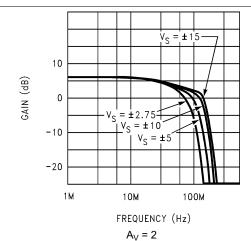
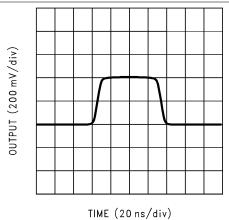


Figure 5-93. Closed-Loop Frequency Response vs Supply Voltage



 $A_V = 2, V_S = \pm 15 V$

Figure 5-90. Small-Signal Pulse Response

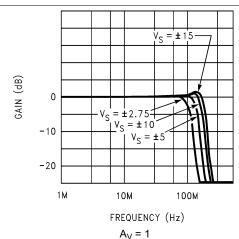


Figure 5-92. Closed-Loop Frequency Response vs Supply Voltage

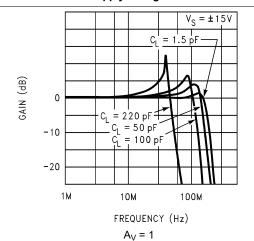


Figure 5-94. Closed-Loop Frequency Response vs Capacitive Load



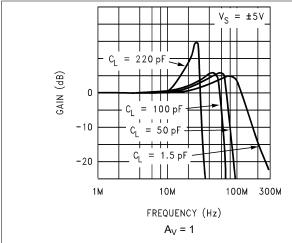


Figure 5-95. Closed Loop Frequency Response vs Capacitive Load

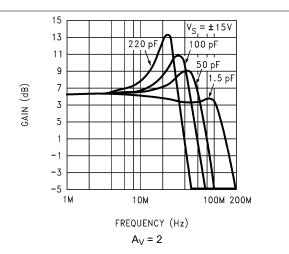


Figure 5-96. Closed-Loop Frequency Response vs Capacitive Load

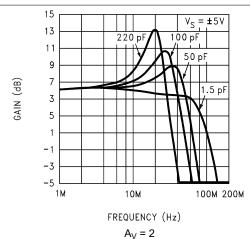


Figure 5-97. Closed-Loop Frequency Response vs Capacitive Load

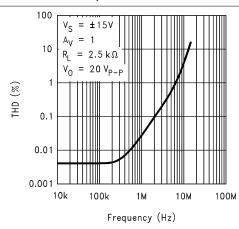


Figure 5-98. Total Harmonic Distortion vs Frequency

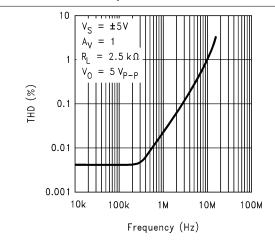


Figure 5-99. Total Harmonic Distortion vs Frequency

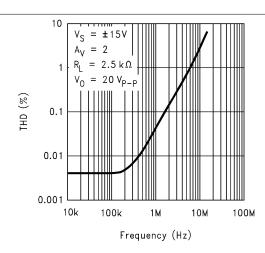


Figure 5-100. Total Harmonic Distortion vs Frequency

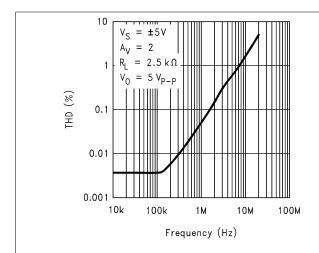


Figure 5-101. Total Harmonic Distortion vs Frequency

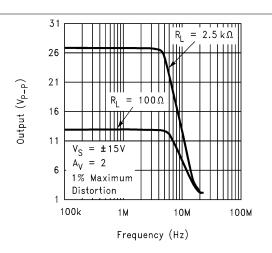


Figure 5-102. Undistorted Output Swing vs Frequency

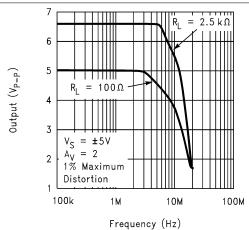


Figure 5-103. Undistorted Output Swing vs Frequency

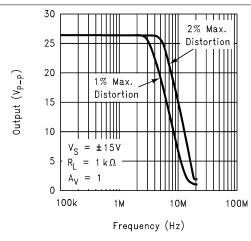


Figure 5-104. Undistorted Output Swing vs Frequency

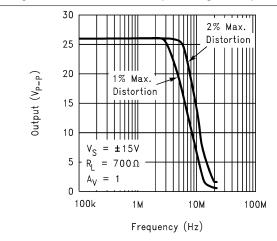


Figure 5-105. Undistorted Output Swing vs Frequency

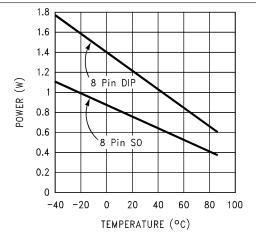


Figure 5-106. Total Power Dissipation vs Ambient Temperature

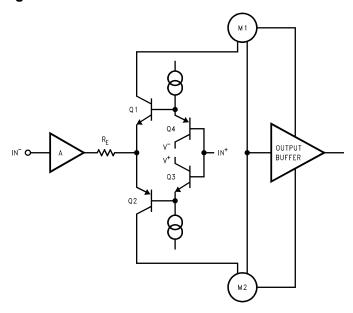
6 Detailed Description

6.1 Overview

The LM6171 is a high-speed, unity-gain-stable voltage-feedback amplifier. The device consumes only 2.5 mA of supply current while providing a gain-bandwidth product of 100 MHz and a slew rate of 3600 V/µs. The LM6171 has additional features, such as low differential gain and phase, and high output current. The LM6171 is a great choice in high-speed circuits.

The LM6171 is a true voltage-feedback amplifier. Unlike current-feedback amplifiers (CFAs) with a low inverting input impedance and a high noninverting input impedance, both inputs of voltage-feedback amplifiers (VFAs) have high-impedance nodes. The low-impedance inverting input in CFAs couples with a feedback capacitor and causes oscillation. As a result, CFAs cannot be used in traditional op-amp circuits, such as photodiode amplifiers, I-to-V converters, and integrators.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Circuit Operation

The class AB input stage in the LM6171 is fully symmetrical and has a similar slewing characteristic to the current feedback amplifiers. In the Section 6.2, Q1 through Q4 form the equivalent of the current feedback input buffer, R_E forms the equivalent of the feedback resistor, and stage A buffers the inverting input. The triple-buffered output stage isolates the gain stage from the load to provide low output impedance.

6.3.2 Slew Rate

The slew rate of the LM6171 is determined by the current available to charge and discharge an internal high impedance node capacitor. The current is the differential input voltage divided by the total degeneration resistor $R_{\rm E}$. Therefore, the slew rate is proportional to the input voltage level, and higher slew rates are achievable in lower-gain configurations.

When a very fast, large signal pulse is applied to the input of an amplifier, some overshoot or undershoot occurs. By placing an external series resistor, such as 1 k Ω , to the input of the LM6171, the bandwidth is reduced to help reduce overshoot.

6.4 Device Functional Modes

The LM6171 has a single functional mode and can be used with both single-supply or split power-supply configurations. The power-supply voltage must be greater than $9 \text{ V} (\pm 4.5 \text{ V})$ and less than $33 \text{ V} (\pm 16.5 \text{ V})$.

Product Folder Links: *LM6171*



7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

7.1.1 Compensation for Input Capacitance

The combination of an amplifier input capacitance and gain setting resistors adds a pole that can cause peaking or oscillation. To solve this problem, use a feedback capacitor with the following value to cancel that pole:

$$C_{F} > \frac{R_{G} \times C_{IN}}{R_{F}} \tag{1}$$

For the LM6171, a feedback capacitor of 2 pF is recommended. Figure 7-1 illustrates the compensation circuit.

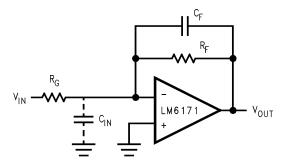


Figure 7-1. Compensating for Input Capacitance



7.1.2 Power Supply Bypassing

Bypassing the power supply is necessary to maintain low power-supply impedance across frequency. Individually bypass both positive and negative power supplies by placing 0.01-µF ceramic capacitors directly to power-supply pins and 2.2-µF tantalum capacitors close to the power-supply pins.

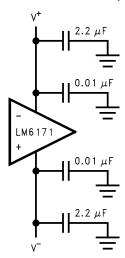
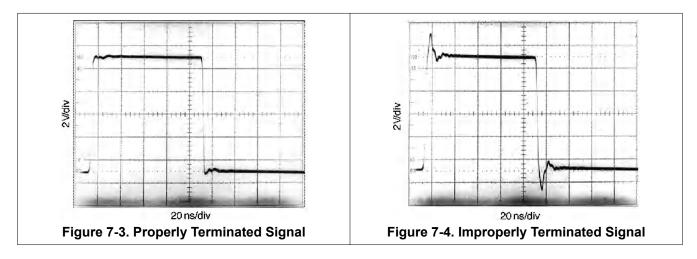


Figure 7-2. Power Supply Bypassing

7.1.3 Termination

In high-frequency applications, reflections occur if signals are not properly terminated. Figure 7-3 shows a properly terminated signal and Figure 7-4 shows an improperly terminated signal.



To minimize reflection, use coaxial cable with matching characteristic impedance to the signal source. Terminate the other end of the cable with the same value terminator or resistor. For commonly used cables, RG59 has a $75-\Omega$ characteristic impedance, and RG58 has a $50-\Omega$ characteristic impedance.

7.1.4 Driving Capacitive Loads

Amplifiers driving capacitive loads can oscillate or have ringing at the output. To eliminate oscillation or reduce ringing, place an isolation resistor as shown in Figure 7-5. The combination of the isolation resistor and the load capacitor forms a pole to increase stability by adding more phase margin to the overall system. The desired performance depends on the value of the isolation resistor; the bigger the isolation resistor, the more damped the pulse response becomes. For the LM6171, a $50-\Omega$ isolation resistor is recommended for initial evaluation. Figure 7-6 shows the LM6171 driving a 200-pF load with the $50-\Omega$ isolation resistor.

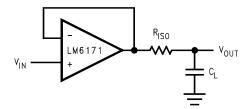


Figure 7-5. Isolation Resistor Used to Drive Capacitive Load

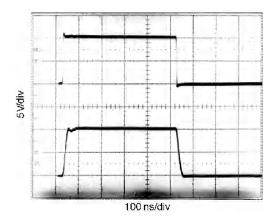


Figure 7-6. The LM6171 Driving a 200-pF Load With a 50- Ω Isolation Resistor

7.1.5 Using Probes

Active (FET) probes are an excellent choice for taking high-frequency measurements because of a wide bandwidth, high input impedance, and low input capacitance. However, the probe ground leads provide a long ground loop that produces errors in measurement. Instead, ground the probes directly by removing the ground leads and probe jackets and using scope probe jacks.

7.1.6 Components Selection and Feedback Resistor

In high-speed applications, keep all component leads short because wires are inductive at high frequency. For discrete components, choose carbon composition-type resistors and mica-type capacitors. Surface-mount components are preferred over discrete components for minimum inductive effect.

Large values of feedback resistors can couple with parasitic capacitance and cause undesirable effects such as ringing or oscillation in high-speed amplifiers. For the LM6171, a feedback resistor of 510 Ω gives optimized performance.



7.2 Typical Applications

7.2.1 Fast Instrumentation Amplifier

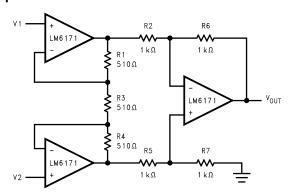


Figure 7-7. Fast Instrumentation Amplifier

$$\begin{split} &V_{IN} = V2 - V1 \\ &\text{if R6} = R2, \ R7 = R5 \ \text{and} \ R1 = R4 \\ &\frac{V_{OUT}}{V_{IN}} = \frac{R6}{R2} \Big(1 + 2 \frac{R1}{R3} \Big) = 3 \end{split}$$

7.2.2 Multivibrator

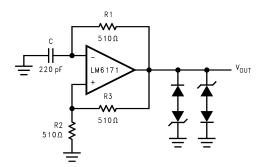


Figure 7-8. Multivibrator

$$f = \frac{1}{2\left(R1C \ln\left[1 + 2\frac{R2}{R3}\right]\right)}$$
$$f = 4 \text{ MHz}$$

7.2.3 Pulse Width Modulator

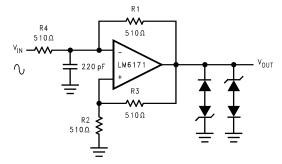


Figure 7-9. Pulse Width Modulator

Submit Document Feedback

7.3 Power Supply Recommendations

7.3.1 Power Dissipation

The maximum power allowed to dissipate in a device is defined as:

$$P_{D} = \frac{T_{J(max)} - T_{A}}{\theta_{JA}}$$
 (2)

where

- P_D is the power dissipation in a device
- $T_{J(max)}$ is the maximum junction temperature
- T_A is the ambient temperature
- θ_{JA} is the thermal resistance of a particular package

For example, for the LM6171 in a SOIC-8 package, the maximum power dissipation at 25°C ambient temperature is 730 mW.

Thermal resistance, θ_{JA} , depends on parameters such as die size, package size, and package material. The smaller the die size and package, the higher θ_{JA} becomes. The 8-pin PDIP package has a lower thermal resistance (108°C/W) than the 8-pin SOIC-8 (172°C/W). Therefore, for higher dissipation capability, use an 8-pin PDIP package.

The total power dissipated in a device can be calculated as:

$$P_D = P_O + P_L \tag{3}$$

where

- P_Q = the quiescent power dissipated in a device with no load connected at the output.
 - P_O = supply current × total supply voltage with no load
- P_L = the power dissipated in the device with a load connected at the output; P_L is not the power dissipated by the load.
 - P_I = output current × (voltage difference between supply voltage and output voltage of the same supply)

For example, the total power dissipated by the LM6171 with $V_S = \pm 15$ V, and the output voltage of 10 V into a 1-k Ω load resistor (one end tied to ground) is:

$$P_D = P_Q + P_L$$
= (2.5 mA) × (30 V) + (10 mA) × (15 V - 10 V)
= 75 mW + 50 mW
= 125 mA

7.4 Layout

7.4.1 Layout Guidelines

7.4.1.1 Printed Circuit Boards and High-Speed Op Amps

There are many things to consider when designing a printed circuit board (PCB) for high-speed op amps. Without proper caution, excessive ringing, oscillation, and other degraded ac performance in high-speed circuits can be frustrating. As a rule, keep the signal traces short and wide to provide low inductance and low-impedance paths. Ground any unused board space to reduce stray signal pickup. Also ground any critical components at a common point to eliminate voltage drop. Sockets add capacitance to the board and can affect frequency performance. If possible, solder the amplifier directly into the PCB without using any socket.



8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

PAL® is a registered trademark of and used under lisence from Advanced Micro Devices, Inc..

All trademarks are the property of their respective owners.

8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

Submit Document Feedback

Copyright © 2023 Texas Instruments Incorporated



9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision C (March 2013) to Revision D (November 2023)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Added the Pin Configuration and Functions, Specifications, ESD Ratings, Thermal Information, Detailed	1
	Description, Application and Implementation, Power Supply Recommendations, Layout, Device and	
	Documentation Support, and Mechanical, Packaging, and Orderable Information sections	1
•	Changed wide unity-gain bandwidth product from 100 MHz to 76 MHz in Features	
•	Changed –3-dB frequency from 62 MHz to 75 MHz in Features	
•	Deleted text stating that LM6171 is developed in TI's vertically integrated process	
•	Changed Operating Ratings to Recommended Operating Conditions and moved Thermal Resistance co	
	to new Thermal Information section	
•	Deleted ESD information and footnote from Absolute Maximum Ratings and moved to ESD Ratings	3
•	Deleted footnote from Recommended Operating Conditions	
•	Changed DC and AC specifications tables to <i>Electrical Characteristics</i> : ±15 V	4
•	Changed LM6171A unity-gain bandwidth from 100 MHz to 76 MHz in Electrical Characteristics: ±15 V	
•	Changed LM6171A -3 -dB freq for A _V = +1 from 160 MHz to 200 MHz in <i>Electrical Characteristics</i> : ± 15	
•	Changed LM6171A –3-dB freq for $A_V = +2$ from 62 MHz to 75 MHz in <i>Electrical Characteristics:</i> $\pm 15 V$.	4
•	Changed LM6171A phase margin from 40° to 58° in <i>Electrical Characteristics:</i> ±15 V	4
•	Changed LM6171A settling time from 48 ns to 21 ns in <i>Electrical Characteristics</i> : ±15 V	4
•	Changed LM6171A propagation delay from 6 ns to 4.1 ns in Electrical Characteristics: ±15 V	4
•	Changed 5 V DC and AC specifications tables to Electrical Characteristics: ±5 V	6
•	Changed LM6171A input common-mode voltage from ±3.7 V to ±3.2 V in <i>Electrical Characteristics</i> : ±5	
•	Changed LM6171A -3 -dB frequency for $A_V = +1$ from 130 MHz to 190 MHz in <i>Electrical Characteristics</i>	: ±5 V
		6
•	Changed LM6171A -3 -dB frequency for A _V = +2 from 45 MHz to 75 MHz in <i>Electrical Characteristics</i> : \pm	5 V . 6
•	Changed LM6171A settling time from 60 ns to 25 ns in <i>Electrical Characteristics</i> : ±5 V	
•	Changed LM6171A propagation delay from 8 ns to 4.5 ns in <i>Electrical Characteristics:</i> ±5 V	
•	Added new Typical Characteristics section for LM6171A	
C	hanges from Revision B (March 2013) to Revision C (March 2013)	Page
•	Changed National Semiconductor data-sheet layout to Texas Instruments format	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com

9-Nov-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
LM6171AIM/NOPB	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 85	LM61 71AIM
LM6171AIM/NOPB.B	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 85	LM61 71AIM
LM6171AIMX/NOPB	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(L61AIM, LM61) 71AIM
LM6171AIMX/NOPB.B	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(L61AIM, LM61) 71AIM
LM6171BIM/NOPB	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 85	LM61 71BIM
LM6171BIMX/NOPB	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 85	LM61 71BIM
LM6171BIN/NOPB	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	LM6171 BIN
LM6171BIN/NOPB.A	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	LM6171 BIN
LM6171BIN/NOPB.B	Active	Production	PDIP (P) 8	40 TUBE	Yes	NIPDAU	Level-1-NA-UNLIM	-40 to 85	LM6171 BIN

⁽¹⁾ **Status:** For more details on status, see our product life cycle.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.



PACKAGE OPTION ADDENDUM

www.ti.com 9-Nov-2025

(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

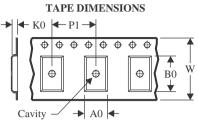
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 18-Jul-2025

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

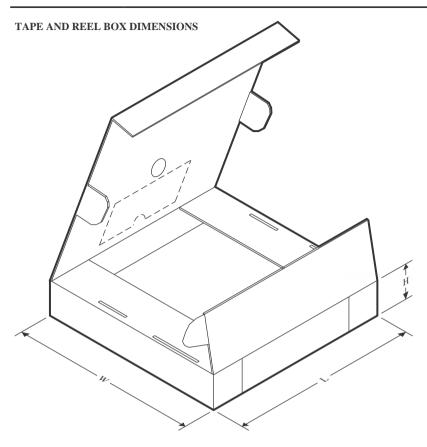


*All dimensions are nominal

Device	_	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM6171AIMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 18-Jul-2025



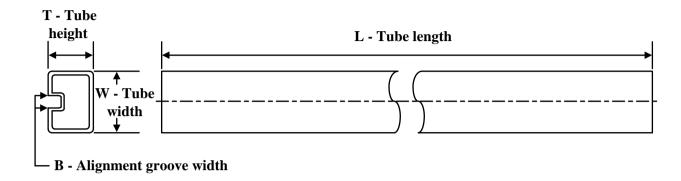
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
LM6171AIMX/NOPB	SOIC	D	8	2500	353.0	353.0	32.0	

PACKAGE MATERIALS INFORMATION

www.ti.com 18-Jul-2025

TUBE



*All dimensions are nominal

	7 III GITTOTOTOTO GI O TTOTTIITGI								
	Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
	LM6171BIN/NOPB	Р	PDIP	8	40	502	14	11938	4.32
ı	LM6171BIN/NOPB.A	Р	PDIP	8	40	502	14	11938	4.32
ĺ	LM6171BIN/NOPB.B	Р	PDIP	8	40	502	14	11938	4.32



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



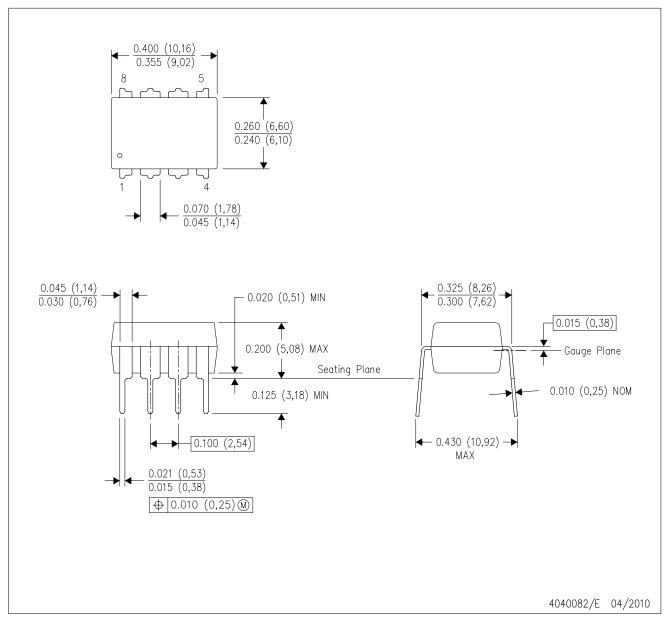
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale, TI's General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025